74HC1G02; 74HCT1G02

2-input NOR gate

Rev. 04 — 11 July 2007 Product data sheet

1. General description

74HC1G02 and 74HCT1G02 are high speed Si-gate CMOS devices. They provide a 2-input NOR function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC02 and 74HCT02.

2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC1G02GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74HCT1G02GW				
74HC1G02GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753
74HCT1G02GV				

4. Marking

Table 2. Marking codes

Type number	Marking
74HC1G02GW	HB
74HCT1G02GW	TB
74HC1G02GV	H02
74HCT1G02GV	T02

5. Functional diagram

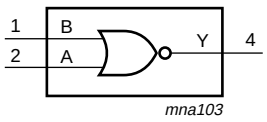


Fig 1. Logic symbol

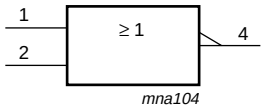


Fig 2. IEC logic symbol

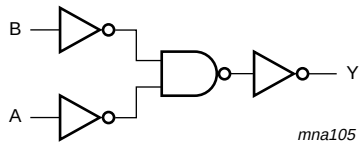


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

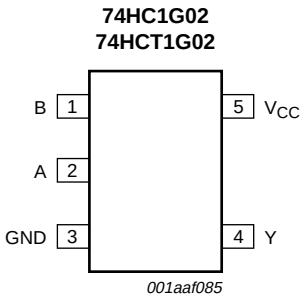


Fig 4. Pin configuration

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B	1	data input
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V_{CC}	5	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Inputs		Output
A	**B**	**Y**
L	L	H
L	H	L
H	L	L
H	H	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7.0	V
I_{IK}	input clamping current	$V_I < –0.5$ V or $V_I > V_{CC} + 0.5$ V		-	±20	mA
I_{OK}	output clamping current	$V_O < –0.5$ V or $V_O > V_{CC} + 0.5$ V		-	±20	mA
I_O	output current	$–0.5 \text{ V} < V_O < V_{CC} + 0.5$ V		-	±12.5	mA
I_{CC}	supply current			-	25	mA
I_{GND}	ground current			–25	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[2]	-	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1G02			74HCT1G02			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	-	139	-	-	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
For type 74HC1G02								
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	V

Table 7. Static characteristics *…continued*

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = –20 µA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	V
		I_O = –20 µA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	V
		I_O = –20 µA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	V
		I_O = –2.0 mA; V_{CC} = 4.5 V	4.13	4.32	-	3.7	-	V
		I_O = –2.6 mA; V_{CC} = 6.0 V	5.63	5.81	-	5.2	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = 20 µA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	V
		I_O = 20 µA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	V
		I_O = 20 µA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	V
		I_O = 2.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
		I_O = 2.6 mA; V_{CC} = 6.0 V	-	0.16	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 6.0 V	-	-	1.0	-	1.0	µA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	10	-	20	µA
C_I	input capacitance		-	1.5	-	-	-	pF
For type 74HCT1G02								
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = –20 µA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	V
		I_O = –2.0 mA; V_{CC} = 4.5 V	4.13	4.32	-	3.7	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = 20 µA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	V
		I_O = 2.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 5.5 V	-	-	1.0	-	1.0	µA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	10	-	20	µA
ΔI_{CC}	additional supply current	per input; V_{CC} = 4.5 V to 5.5 V; V_I = V_{CC} – 2.1 V; I_O = 0 A	-	-	500	-	850	µA
C_I	input capacitance		-	1.5	-	-	-	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

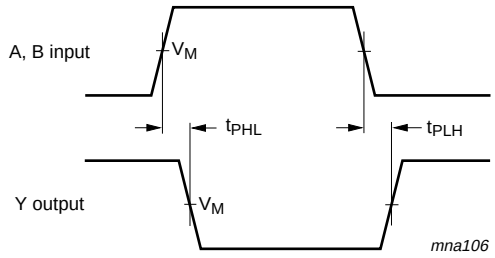
GND = 0 V; $t_r = t_f \leq 6.0$ ns; All typical values are measured at $T_{amb} = 25\,°C$. For test circuit see Figure 6

Symbol	Parameter	Conditions		−40 °C to +85 °C			−40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	
For type 74HC1G02									
t_{pd}	propagation delay	A and B to Y; see Figure 5	[1]						
		V_{CC} = 2.0 V; C_L = 50 pF		-	25	115	-	135	ns
		V_{CC} = 4.5 V; C_L = 50 pF		-	9	23	-	27	ns
		V_{CC} = 5.0 V; C_L = 15 pF		-	7	-	-	-	ns
		V_{CC} = 6.0 V; C_L = 50 pF		-	8	20	-	23	ns
C_{PD}	power dissipation capacitance	V_I = GND to V_{CC}	[2]	-	18	-	-	-	pF
For type 74HCT1G02									
t_{pd}	propagation delay	A and B to Y; see Figure 5	[1]						
		V_{CC} = 4.5 V; C_L = 50 pF		-	11	24	-	27	ns
		V_{CC} = 5.0 V; C_L = 15 pF		-	9	-	-	-	ns
C_{PD}	power dissipation capacitance	V_I = GND to V_{CC} − 1.5 V	[2]	-	19	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL}.

[2] C_{PD} is used to determine the dynamic power dissipation P_D (µW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz
f_o = output frequency in MHz
C_L = output load capacitance in pF
V_{CC} = supply voltage in Volts
$\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs

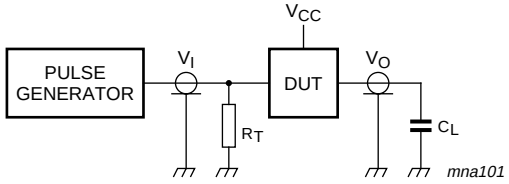
12. Waveforms



For HC1G02: $V_M = 0.5 \times V_{CC}$; V_I = GND to V_{CC}

For HCT1G02: V_M = 1.3 V; V_I = GND to 3.0 V

Fig 5. Input to output propagation delays



Test data is given in Table 8.

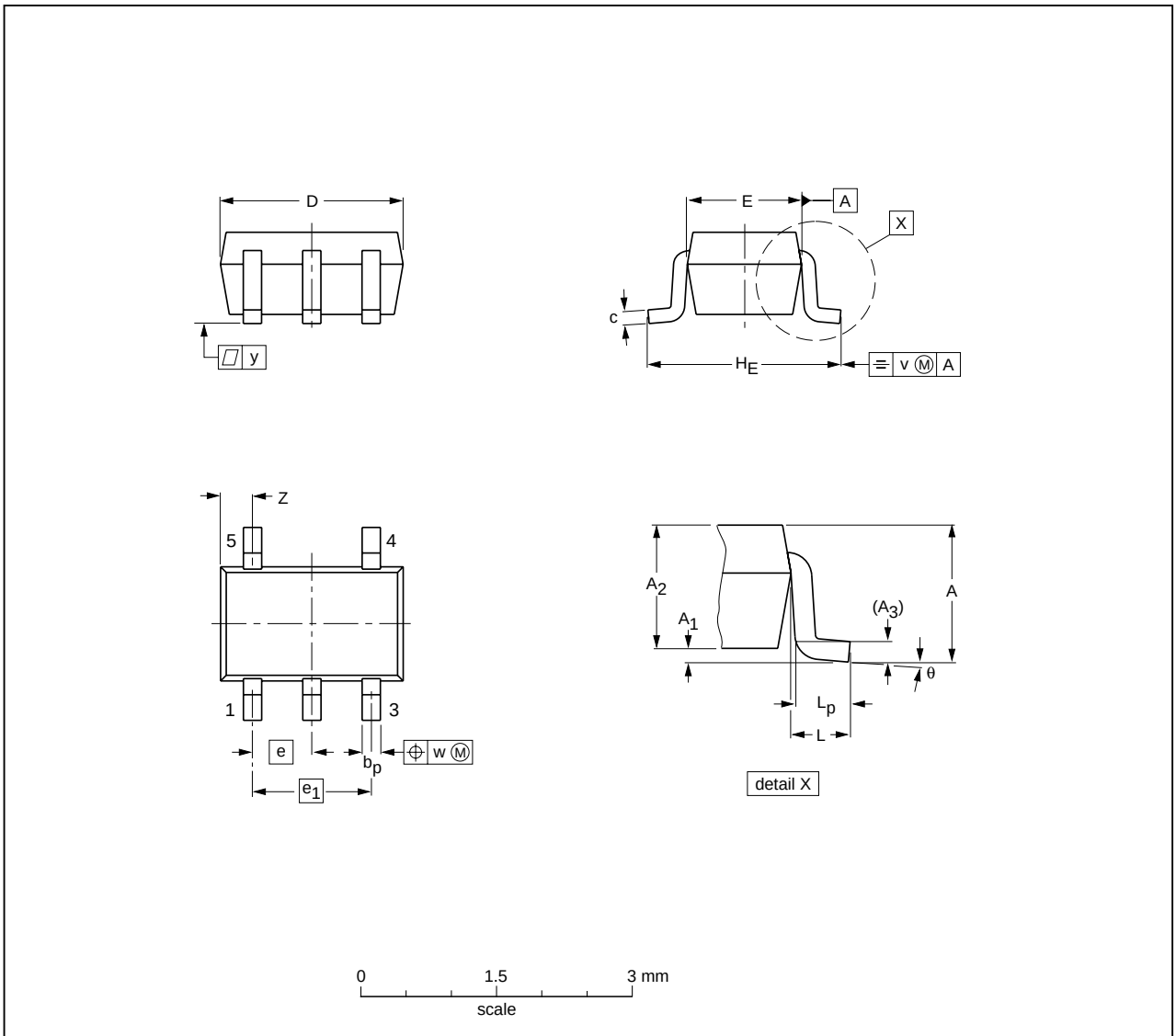
C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 6. Load circuitry for switching times

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm **SOT353-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	e_1	H_E	L	L_p	v	w	y	$Z^{(1)}$	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

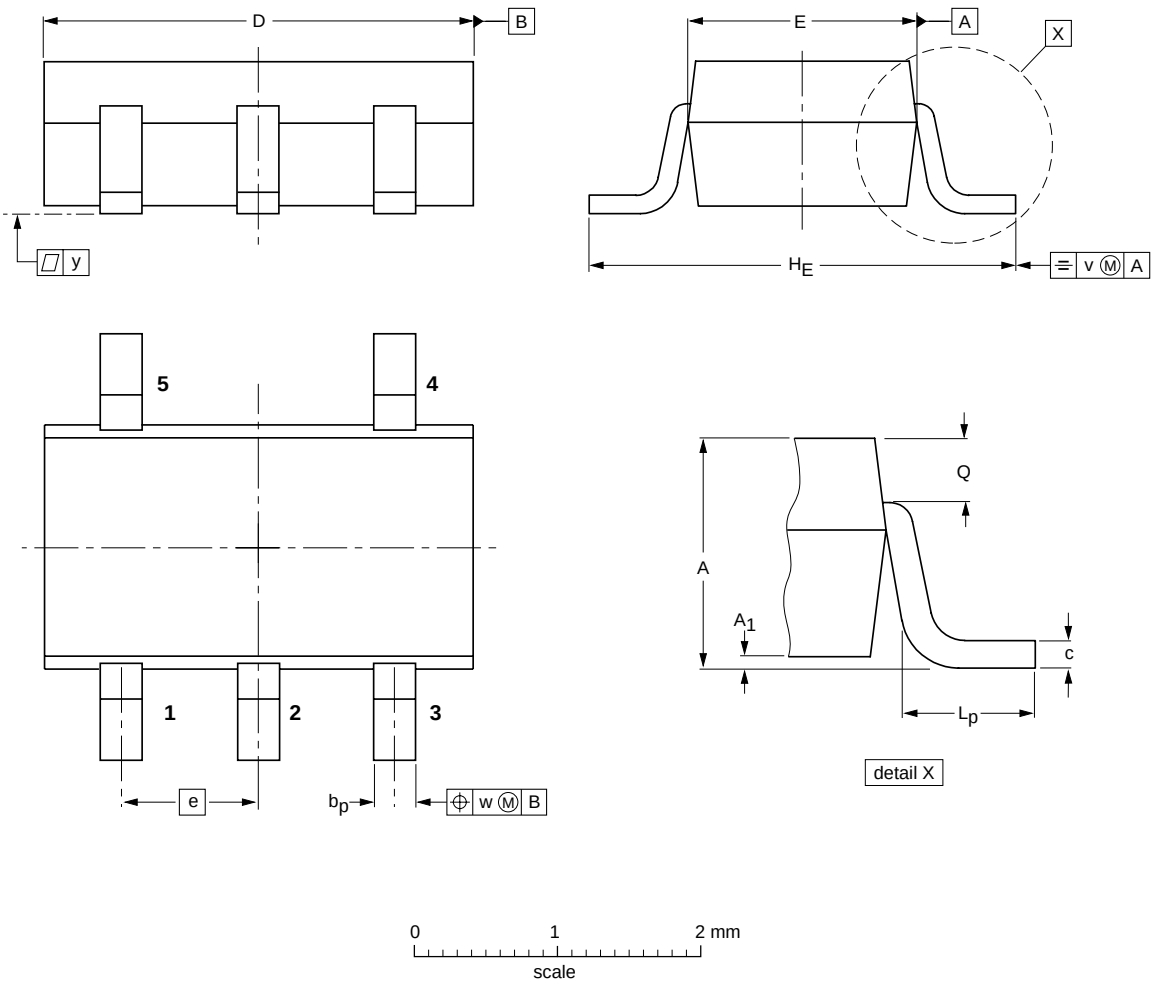
Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT353-1		MO-203	SC-88A			~~00-09-01~~ 03-02-19

Fig 7. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads **SOT753**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	c	D	E	e	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.100 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT753			SC-74A			~~02-04-16~~ 06-03-16

Fig 8. Package outline SOT753 (SC-74A)

14. Abbreviations

Table 9. Abbreviations

Acronym	Description
DUT	Device Under Test
TTL	Transistor-Transistor Logic

15. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G02_4	20070711	Product data sheet	-	74HC_HCT1G02_3
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Package SOT353 changed to SOT353-1 in Table 1 and Figure 7. • Quick reference data and Soldering sections removed. • Section 2 “Features” updated.			
74HC_HCT1G02_3	20020517	Product specification	-	74HC_HCT1G02_2
74HC_HCT1G02_2	20010302	Product specification	-	74HC_HCT1G02_1
74HC_HCT1G02_1	19980831	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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18. Contents

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